IRHMS57064, Test Characteristics

**IRHMS57064 (JANSR2N7470T1)**
60V 100kRad Hi-Rel Single N-Channel TID Hardened MOSFET in a TO-254 Low-Ohmic package

**Electrical Characteristics @ Tj = 25°C,**
RDS(on) [Static Drain-to-Source On-State Resistance], with test condition of VGS = 12V, ID = 45A
Change RDS(on) Max limit from 0.0066 Ω to 0.0076 Ω

**Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation**
RDS(on) [Static Drain-to-Source On-State Resistance], with test condition of VGS = 12V, ID = 45A

For up to 500K Rads(Si), Low-Ohmic TO-254 only
Change RDS(on) Max limit from 0.0066 Ω to 0.0076 Ω

For 1000K Rads (Si), Low-Ohmic TO-254 only
Change RDS(on) Max limit from 0.0070 Ω to 0.0080 Ω

Reference: IR Datasheet PD-95838